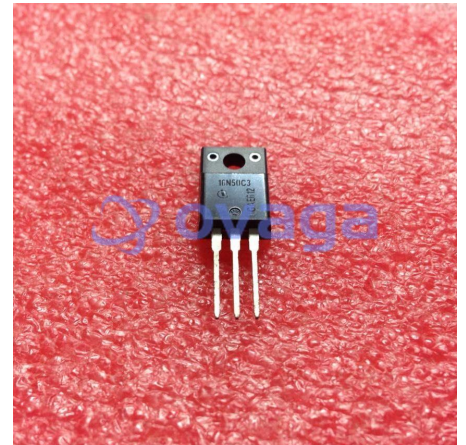


N-Channel MOSFETs >500V...900V; Package: PG-TO220-3; VDS max: 500.0 V;
 Package: TO-220 FullPAK; RDS(on) @ TJ=25°C VGS=10: 280.0 mOhm; IDmax @
 TC=25°C: 16.0 A; IDpuls max: 48.0 A;

Manufacturers	Infineon Technologies Corporation
Package/Case	TO-220F
Product Type	Transistors
RoHS	
Lifecycle	



Images are for reference only

Please submit RFQ for SPA16N50C3 or [Email to us: sales@ovaga.com](mailto:sales@ovaga.com) We will contact you in 12 hours.

[RFQ](#)

General Description

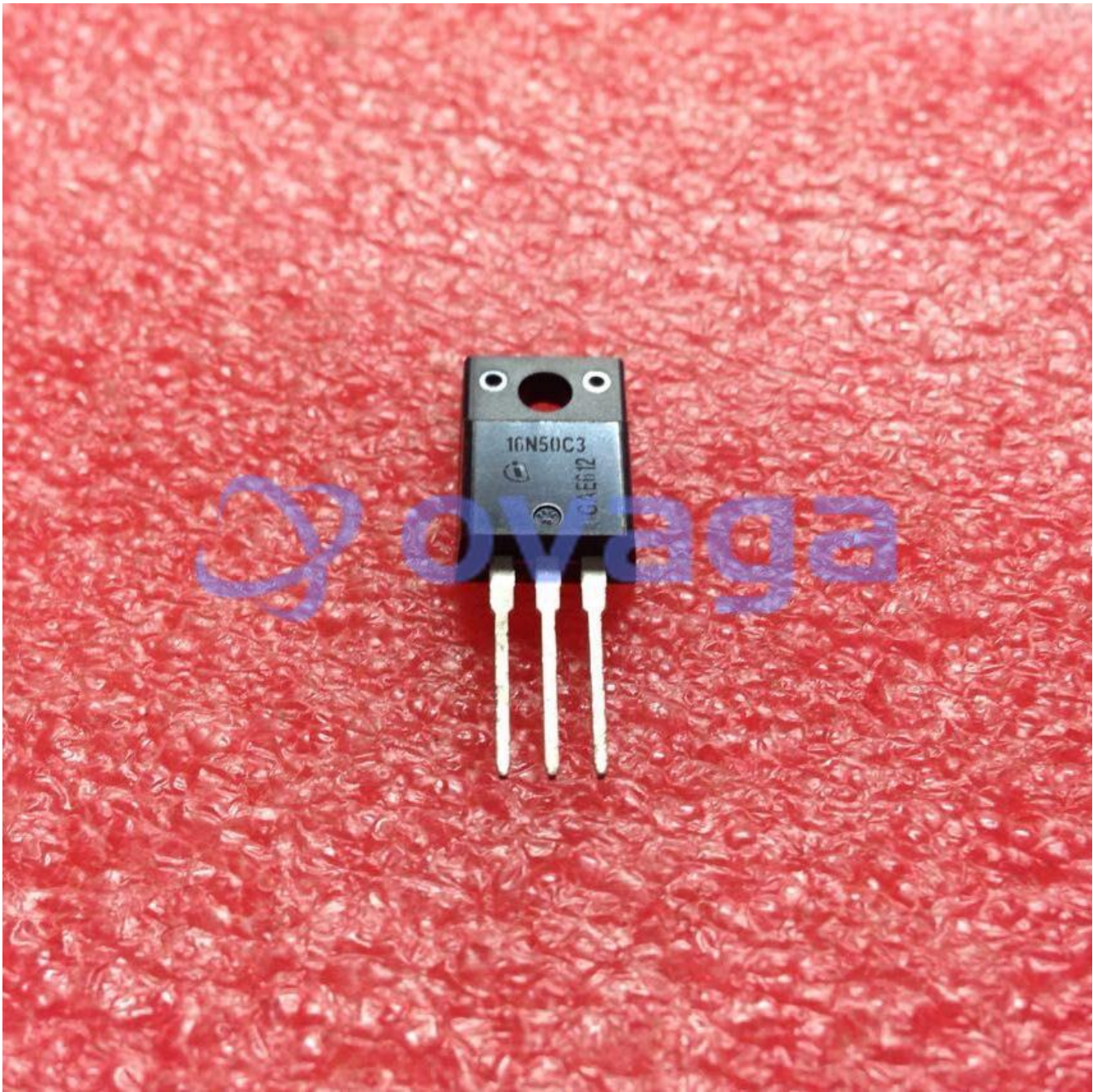
SPA16N50C3 is a MOSFET (Metal-Oxide-Semiconductor Field-Effect Transistor) power transistor manufactured by Infineon Technologies. Here are its features:

Features

- Drain-Source Voltage (Vdss): 560V
- Continuous Drain Current (Id): 16A
- Power Dissipation (Pd): 198W
- Gate-Source Voltage (Vgs): +/- 20V
- Low on-state resistance (Rds(on)): 0.25 Ohm
- Fast switching characteristics
- High input impedance

Application

- Power supplies
- Uninterruptible Power Supplies (UPS)
- Motor control
- DC-DC converters
- Switched-mode power supplies (SMPS)
- Lighting applications



Related Products



[BSP613P](#)

Infineon Technologies Corporation
SOT-223



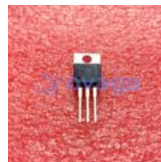
[SPP11N65C3](#)

Infineon Technologies Corporation
TO-220



[SPP07N65C3](#)

Infineon Technologies Corporation
TO-220AB



[SPP07N60S5](#)

Infineon Technologies Corporation
P-TO220-3-1



[SPP11N60C3XKSA1](#)

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[IRF640NSPBF](#)

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PAK-3



[SPD03N60S5](#)

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TO-252



[SPP20N60CFD](#)

Infineon Technologies Corporation
TO-220AB